

Preliminary datasheet

EconoPACK™3 module with Trench/Fieldstop IGBT4 and emitter controlled 4 diode and PressFIT

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{nom}} = 150\text{ A} / I_{CRM} = 300\text{ A}$
 - Low $V_{CE,\text{sat}}$
 - Trench IGBT 4
 - $T_{vj,\text{op}} = 150^\circ\text{C}$
 - $V_{CE,\text{sat}}$ with positive temperature coefficient
- Mechanical features
 - Al_2O_3 substrate with low thermal resistance
 - High power and thermal cycling capability
 - Integrated NTC temperature sensor
 - Copper base plate
 - PressFIT contact technology
 - Standard housing



Typical appearance

Potential applications

- Auxiliary inverters
- Motor drives
- Servo drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

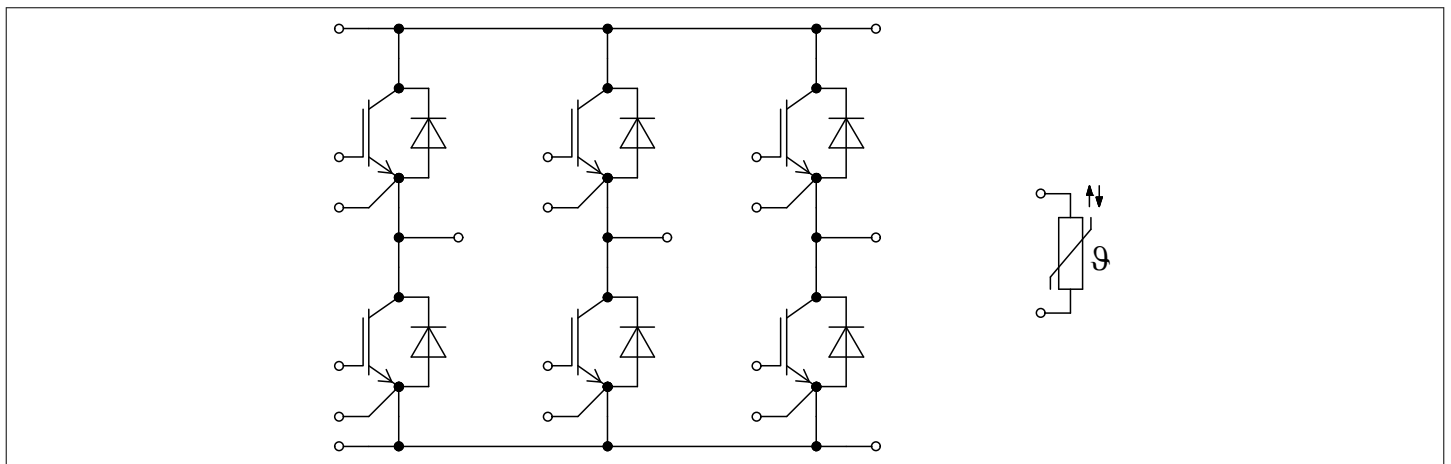


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to heatsink	7.5	mm
Comparative tracking index	CTI		> 200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			21		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25^\circ\text{C}$, per switch		1.8		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	M5, Screw	3	6	Nm
Weight	G			300		g

Note: The current under continuous operation is limited to 50 A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25^\circ\text{C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175^\circ\text{C}$ $T_C = 90^\circ\text{C}$	150	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj \text{ op}}$	300	A
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 150\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.75	2.10	V
			$T_{vj} = 125\ ^\circ C$		2.05		
			$T_{vj} = 150\ ^\circ C$		2.10		
Gate threshold voltage	V_{GETh}	$I_C = 5.3\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.20	5.80	6.40	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V$			1.25		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			5		Ω
Input capacitance	C_{ies}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			9.35		nF
Reverse transfer capacitance	C_{res}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.35		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			1	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 150\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 1.1\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.115		μs
			$T_{vj} = 125\ ^\circ C$		0.130		
			$T_{vj} = 150\ ^\circ C$		0.135		
Rise time (inductive load)	t_r	$I_C = 150\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 1.1\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.025		μs
			$T_{vj} = 125\ ^\circ C$		0.030		
			$T_{vj} = 150\ ^\circ C$		0.030		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 150\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 1.1\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.370		μs
			$T_{vj} = 125\ ^\circ C$		0.450		
			$T_{vj} = 150\ ^\circ C$		0.480		
Fall time (inductive load)	t_f	$I_C = 150\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 1.1\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.060		μs
			$T_{vj} = 125\ ^\circ C$		0.105		
			$T_{vj} = 150\ ^\circ C$		0.125		
Turn-on energy loss per pulse	E_{on}	$I_C = 150\ A, V_{CC} = 600\ V, L_\sigma = 40\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 1.1\ \Omega, di/dt = 6000\ A/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		5		mJ
			$T_{vj} = 125\ ^\circ C$		9		
			$T_{vj} = 150\ ^\circ C$		10		
Turn-off energy loss per pulse	E_{off}	$I_C = 150\ A, V_{CC} = 600\ V, L_\sigma = 40\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 1.1\ \Omega, dv/dt = 3600\ V/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		10		mJ
			$T_{vj} = 125\ ^\circ C$		15		
			$T_{vj} = 150\ ^\circ C$		16		
SC data	I_{SC}	$V_{GE} \leq 15\ V, V_{CC} = 800\ V, V_{CEmax} = V_{CES} - L_{sCE} * di/dt$	$t_P \leq 10\ \mu s, T_{vj} = 150\ ^\circ C$		600		A

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.200	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$		0.0830		K/W
Temperature under switching conditions	T_{vjop}		-40		150	°C

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25 \text{ °C}$	1200	V	
Continuous DC forward current	I_F		150	A	
Repetitive peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$	300	A	
I^2t - value	I^2t	$t_p = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ °C}$	3050	A^2s
			$T_{vj} = 150 \text{ °C}$	2950	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 150 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$	1.70	2.15	V
			$T_{vj} = 125 \text{ °C}$	1.65		
			$T_{vj} = 150 \text{ °C}$	1.65		
Peak reverse recovery current	I_{RM}	$V_{CC} = 600 \text{ V}, I_F = 150 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 6000 \text{ A}/\mu\text{s} (T_{vj} = 150 \text{ °C})$	$T_{vj} = 25 \text{ °C}$	220		A
			$T_{vj} = 125 \text{ °C}$	240		
			$T_{vj} = 150 \text{ °C}$	250		
Recovered charge	Q_r	$V_{CC} = 600 \text{ V}, I_F = 150 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 6000 \text{ A}/\mu\text{s} (T_{vj} = 150 \text{ °C})$	$T_{vj} = 25 \text{ °C}$	14		μC
			$T_{vj} = 125 \text{ °C}$	25		
			$T_{vj} = 150 \text{ °C}$	28		
Reverse recovery energy	E_{rec}	$V_{CC} = 600 \text{ V}, I_F = 150 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 6000 \text{ A}/\mu\text{s} (T_{vj} = 150 \text{ °C})$	$T_{vj} = 25 \text{ °C}$	7		mJ
			$T_{vj} = 125 \text{ °C}$	11.5		
			$T_{vj} = 150 \text{ °C}$	13.5		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per diode			0.375	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$		0.155		K/W
Temperature under switching conditions	T_{vjop}		-40		150	°C

4 NTC-Thermistor

Table 7 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25 \text{ °C}$		5		kΩ
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100 \text{ °C}, R_{100} = 493 \text{ Ω}$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25 \text{ °C}$			20	mW
B-value	$B_{25/50}$			3375		K
B-value	$B_{25/80}$			3411		K
B-value	$B_{25/100}$			3433		K

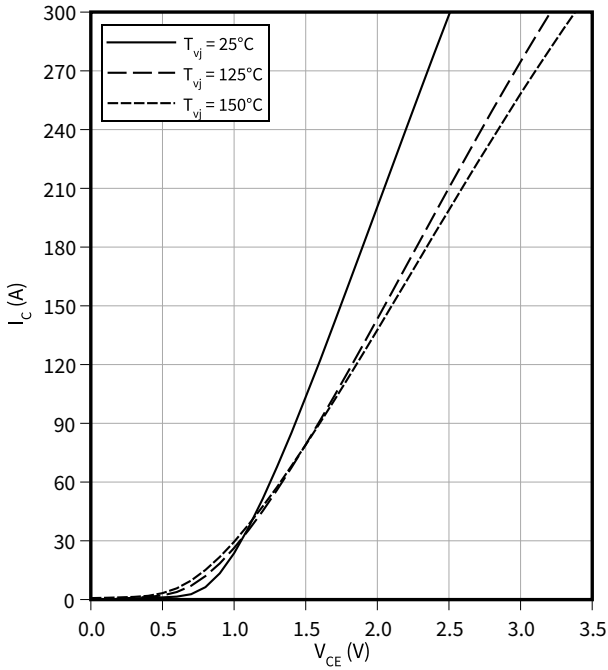
Note: Specification according to the valid application note.

5 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

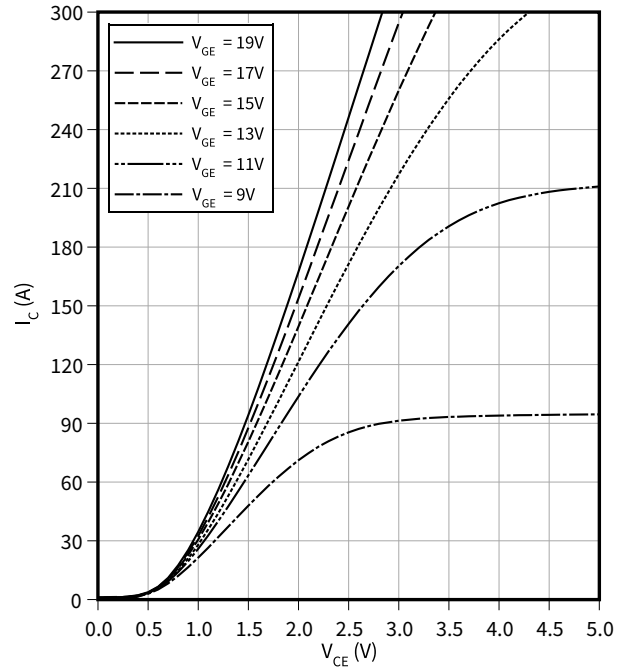
$$V_{GE} = 15 \text{ V}$$



Output characteristic field (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

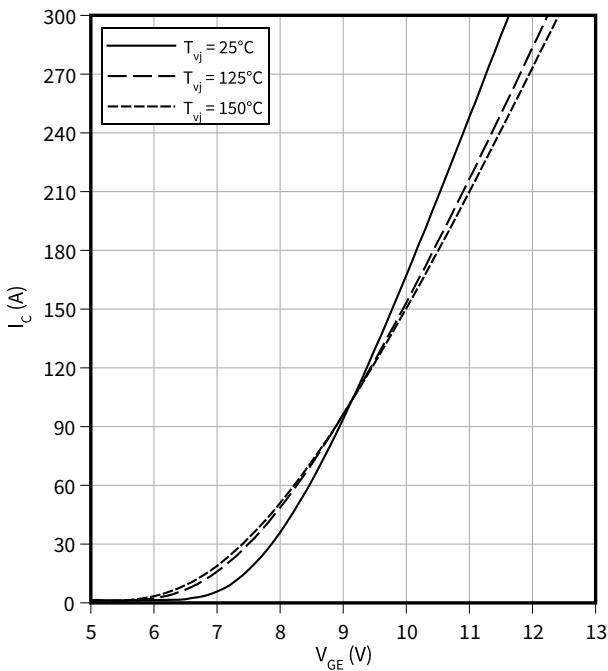
$$T_{vj} = 150 \text{ °C}$$



Transfer characteristic (typical), IGBT, Inverter

$$I_C = f(V_{GE})$$

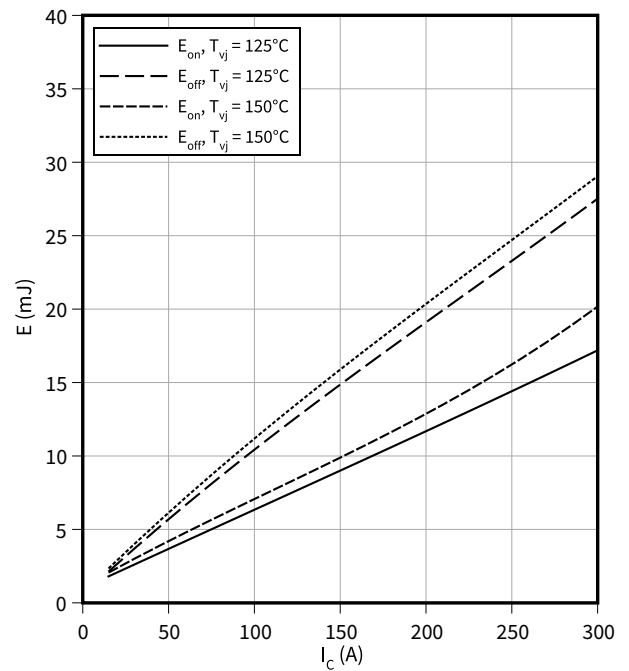
$$V_{CE} = 20 \text{ V}$$



Switching losses (typical), IGBT, Inverter

$$E = f(I_C)$$

$$R_{Goff} = 1.1 \text{ } \Omega, R_{Gon} = 1.1 \text{ } \Omega, V_{GE} = \pm 15 \text{ V}, V_{CC} = 600 \text{ V}$$

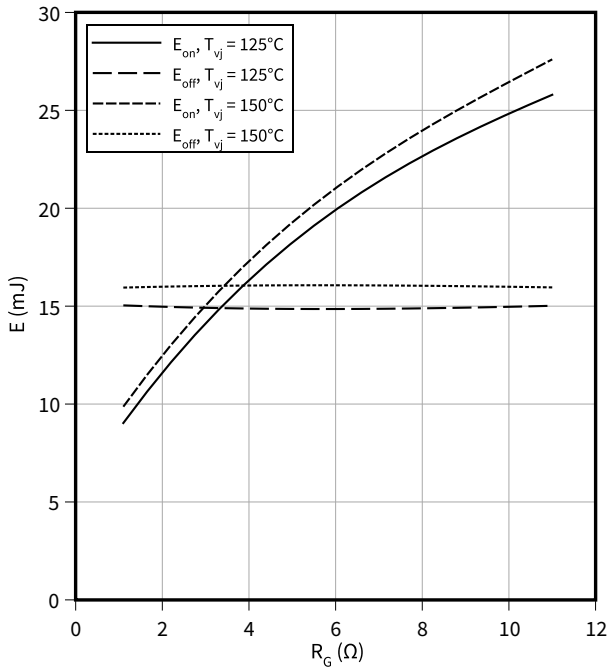


5 Characteristics diagrams

Switching losses (typical), IGBT, Inverter

$E = f(R_G)$

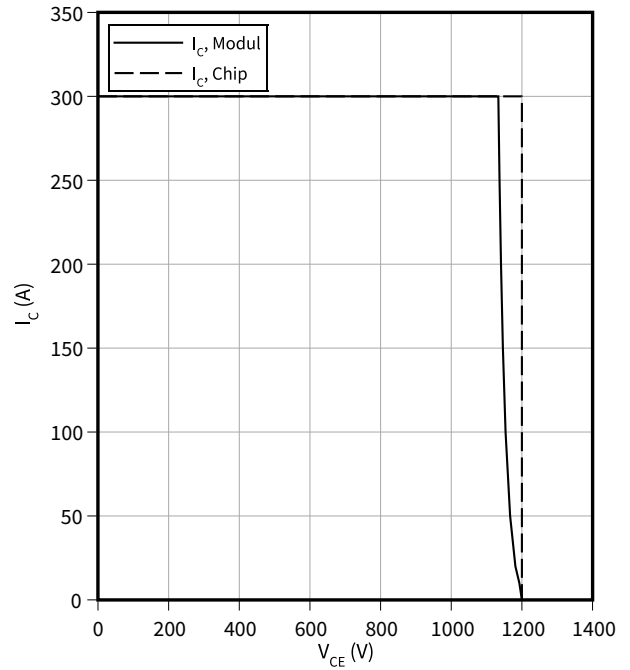
$V_{GE} = \pm 15 \text{ V}$, $I_C = 150 \text{ A}$, $V_{CC} = 600 \text{ V}$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

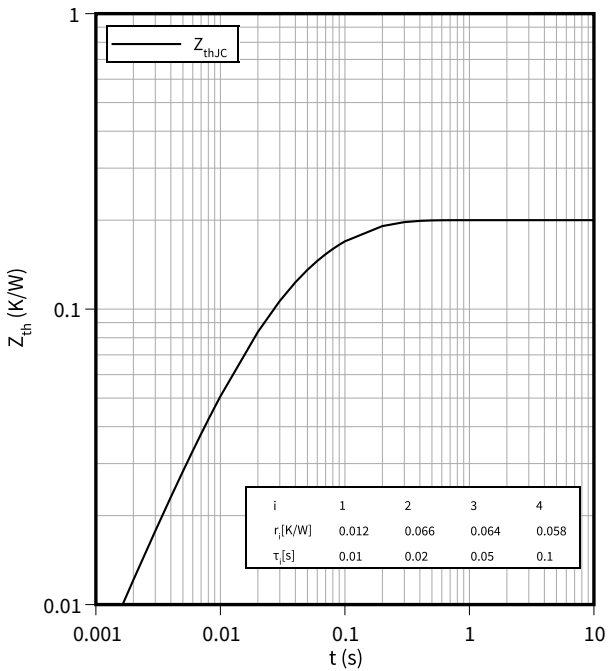
$I_C = f(V_{CE})$

$R_{Goff} = 1.1 \Omega$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 150 \text{ °C}$



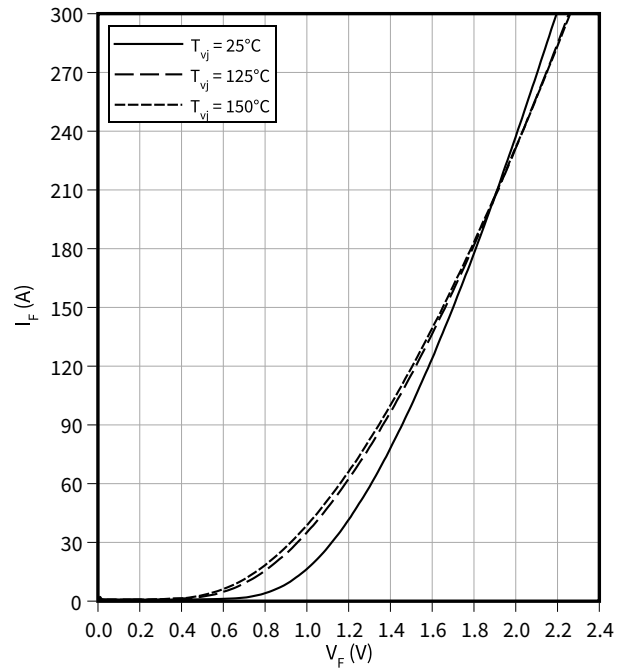
Transient thermal impedance, IGBT, Inverter

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, Inverter

$I_F = f(V_F)$

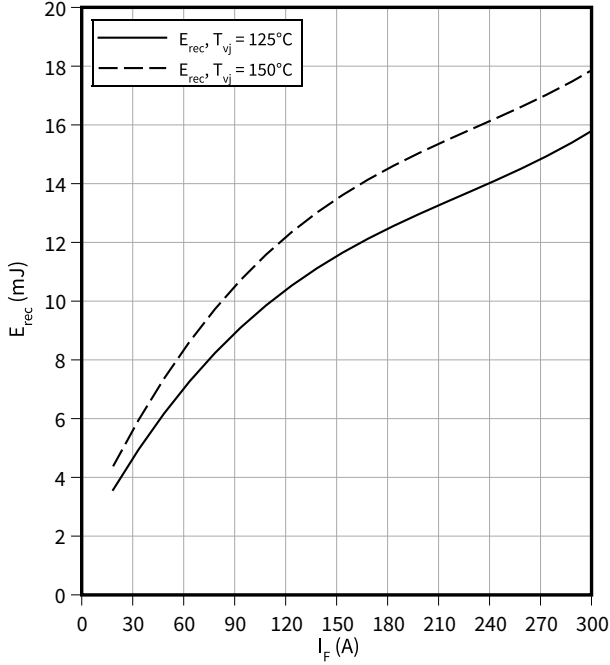


5 Characteristics diagrams

Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

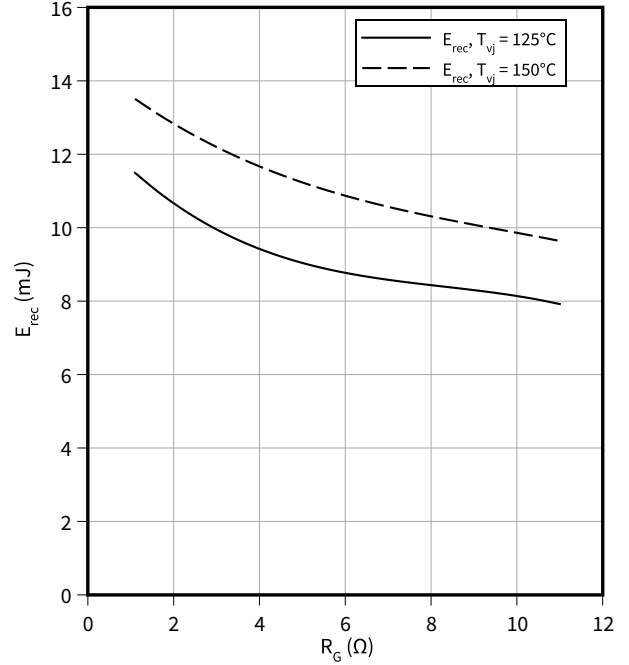
$R_{Gon} = 1.1 \Omega, V_{CC} = 600 V$



Switching losses (typical), Diode, Inverter

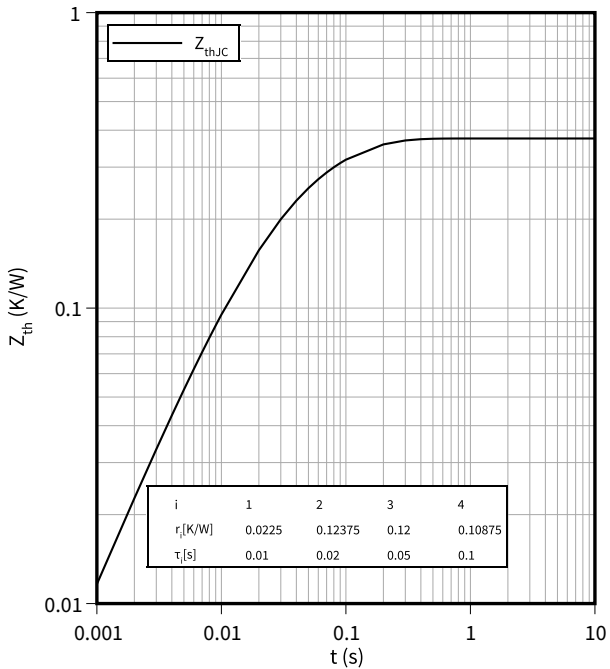
$E_{rec} = f(R_G)$

$I_F = 150 A, V_{CC} = 600 V$



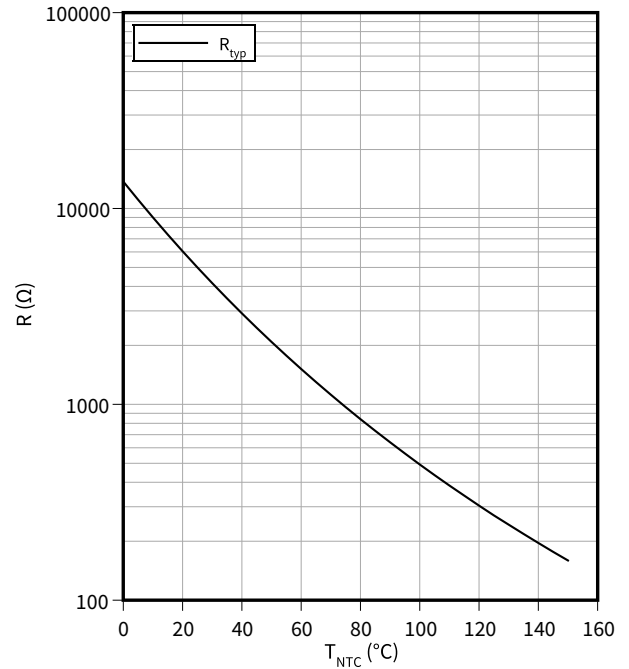
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



6 Circuit diagram

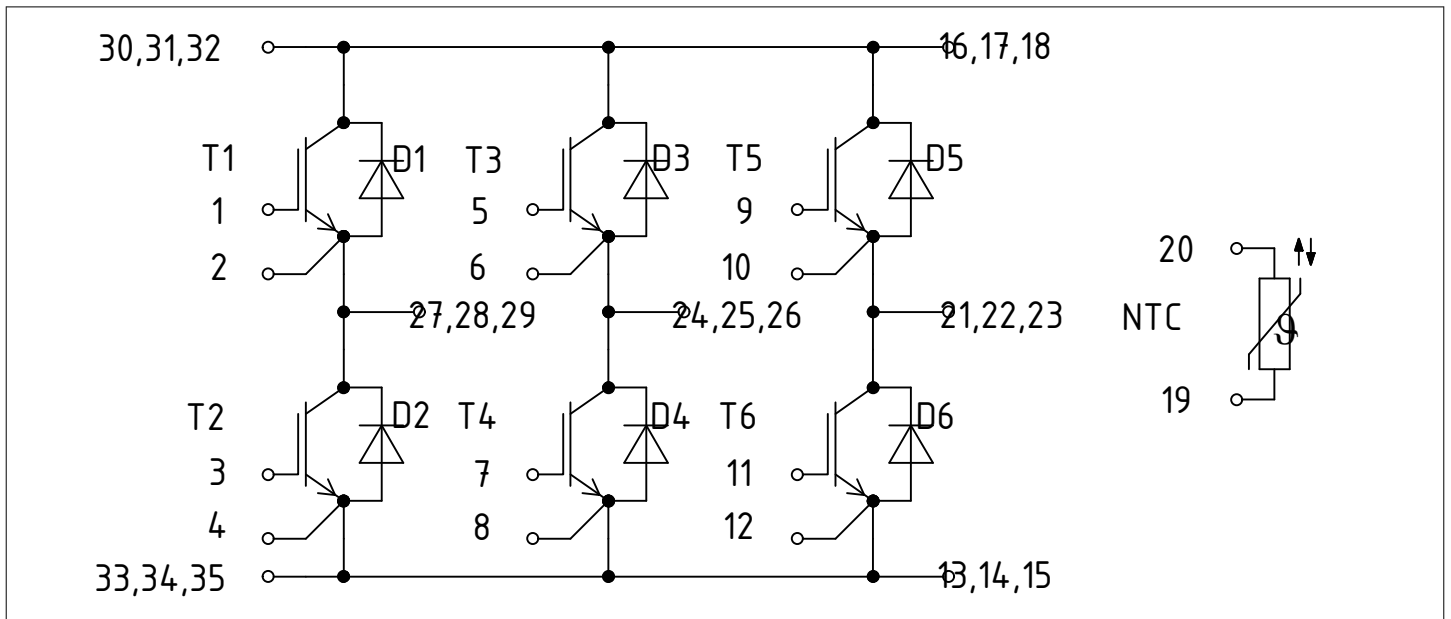


Figure 1

8 Module label code


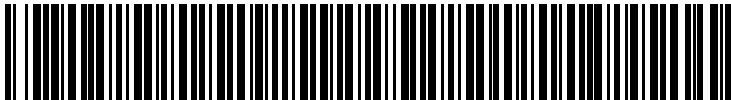
Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 - 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 - 21	15
	Date code (production week)	22 - 23	30
Example	 		
	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
V1.0	2006-05-11	Target datasheet
V1.1	2006-11-06	Target datasheet
V1.2	2007-03-19	Target datasheet
V1.3	2007-05-21	Target datasheet
V2.0	2007-10-29	Preliminary datasheet
V2.1	2009-03-06	Preliminary datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
0.20	2024-08-27	Preliminary datasheet

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